

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings of claims in the application.

1. (Previously presented) A method of washing a photomask comprising:
removing organic matter and metal impurities present on the surface of a photomask;
removing foreign matter adhering to said surface of said photomask with H₂ gas

dissolved water; and

drying said photomask,

wherein said photomask is a phase-shift mask including halftone mask, said H₂ gas dissolved water contains ammonia and the concentration of said ammonia is not more than 1%.

2. (Original) The method of washing a photomask in accordance with claim 1, wherein said H₂ gas dissolved water is alkalized.

3. (Original) The method of washing a photomask in accordance with claim 2, wherein said H₂ gas dissolved water is alkalized with ammonia.

4. (Cancelled)

5. (Previously presented) The method of washing a photomask in accordance with claim 1, also employing ultrasonics waves in said step of removing foreign matter.

6. (Previously presented) The method of washing a photomask in accordance with claim 5, wherein said step of removing organic matter and metal impurities employs ultrasonics waves.

7. (Previously presented) The method of washing a photomask in accordance with claim 5, wherein said foreign matter is particulate foreign matter.

8-14. (Cancelled)

15. (Previously presented) The method of washing a photomask in accordance with claim 1, wherein said phase-shift photomask is formed with an MoSiON film.